

# [DOUBLE-TRIGGERED SILICON CONTROLLING RECTIFIER AND ELECTROSTATIC DISCHARGE PROTECTION CIRCUIT THEREOF]

## Abstract

A double-triggered silicon controller rectifier (SCR) comprises a plurality of N+ diffusion areas, a plurality of P+ diffusion areas, a first N-well region, a second N-well region and a third N-well region formed in a P-substrate. The N+ diffusion areas and the P+ diffusion areas are isolated by shallow trench isolation (STI) structures. Two of the N+ diffusion areas are N-type trigger terminals. Two of the P+ diffusion areas are the P-type trigger terminal.